BTA312-800ET

3Q Hi-Com Triac

Rev. 02 — 2 December 2010

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package. The "series ET" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series ET" is intended for interfacing with low power drivers including microcontrollers where "high junction operating temperature" capability is required.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

1.4 Quick reference data

Table 1. Quick reference data

| Table 1. | Quick reference data | | | | | |
|------------------|---|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V_{DRM} | repetitive peak off-state voltage | | - | - | 800 | V |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see Figure 4; see Figure 5 | - | - | 95 | Α |
| Ti | iunction temperature | | - | - | 150 | °C |



Table 1. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|----------------------|---|-----|-----|-----|------|
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{mb} \le 126 ^{\circ}\text{C}$; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u> | - | - | 12 | Α |
| Static char | acteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | - | - | 10 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | - | - | 10 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | - | - | 10 | mA |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|--------------------|----------------|
| 1 | T1 | main terminal 1 | | N. |
| 2 | T2 | main terminal 2 | mb | T2T1 |
| 3 | G | gate | | sym051 |
| mb | T2 | mounting base; main terminal 2 | 1 2 3 | |
| | | | SOT78 (TO-220AB) | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|----------|--|---------|
| | Name | Description | Version |
| BTA312-800ET | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| | | • | | | |
|---------------------|---|---|-----|-----|------------------|
| Symbol | Parameter | Conditions | Min | Max | Unit |
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; T _{mb} ≤ 126 °C; see <u>Figure 3;</u> see <u>Figure 1;</u> see <u>Figure 2</u> | - | 12 | Α |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u> | - | 95 | Α |
| | | full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$ | - | 105 | Α |
| I ² t | l ² t for fusing | t _p = 10 ms; sine-wave pulse | - | 45 | A ² s |
| dI _T /dt | rate of rise of on-state current | $I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$ | - | 100 | A/µs |
| I_{GM} | peak gate current | | - | 2 | Α |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 150 | °C |
| | | | | | |

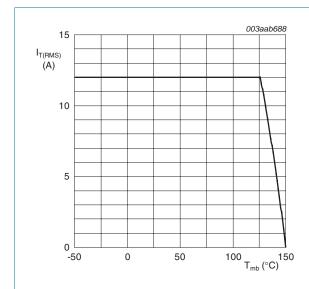
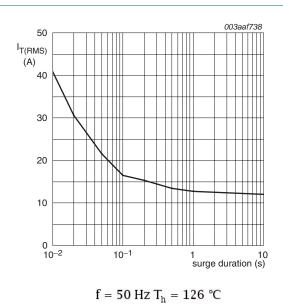


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



ig 2. RMS on-state current as a function of surge

duration; maximum values

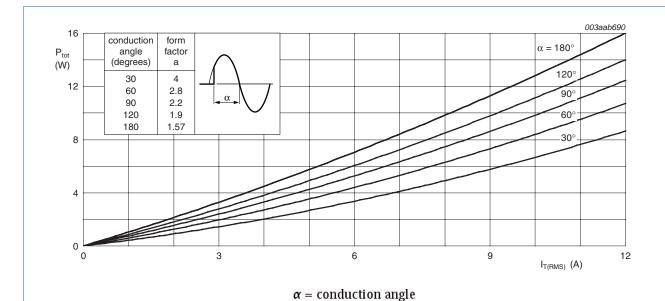


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

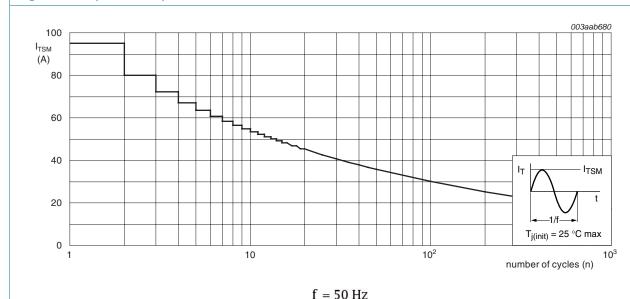
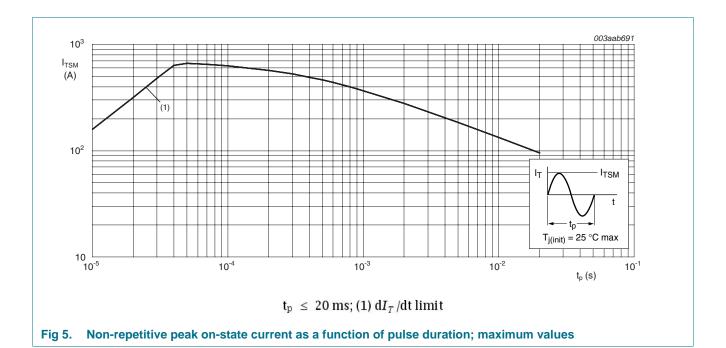


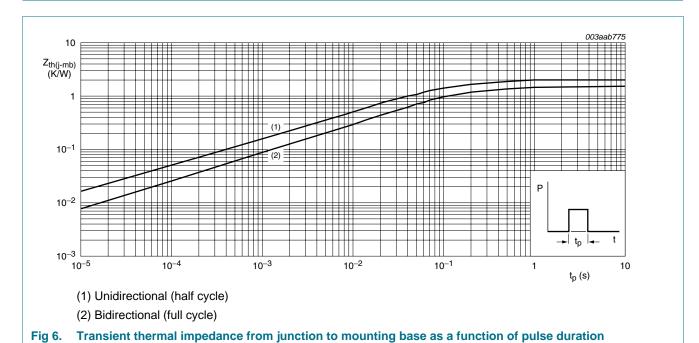
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|--------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; see Figure 6 | - | - | 1.5 | K/W |
| | | half cycle; see Figure 6 | - | - | 2 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |



6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--|------|-----|-----|------|
| Static cha | racteristics | | | | | |
| I _{GT} gate | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see Figure 7 | - | - | 10 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G-; T_j = 25 \text{ °C;}$ see Figure 7 | - | - | 10 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-; } T_j = 25 \text{ °C;}$ see Figure 7 | - | - | 10 | mA |
| lL | latching current | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+G+; T_j = 25 \text{ °C;}$ see Figure 8 | - | - | 25 | mA |
| | | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G-; T_j = 25 \text{ °C;}$ see Figure 8 | - | - | 30 | mA |
| | | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-; } T_j = 25 \text{ °C;}$ see <u>Figure 8</u> | - | - | 25 | mA |
| I _H | holding current | $V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{Minimum of the properties of the properti$ | - | - | 15 | mΑ |
| V_{T} | on-state voltage | $I_T = 15 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{\text{ colored}}$ | - | 1.3 | 1.6 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11 | - | 0.7 | 1.5 | V |
| | | $V_D = 400 \text{ V; } I_T = 0.1 \text{ A; } T_j = 150 \text{ °C;}$ see Figure 11 | 0.25 | - | - | V |
| I _D | off-state current | $V_D = 800 \text{ V}; T_j = 150 ^{\circ}\text{C}$ | - | 0.4 | 2 | mΑ |
| Dynamic o | characteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 536 V; T_j = 150 °C; exponential waveform; gate open circuit | 30 | - | - | V/µs |
| dl _{com} /dt | rate of change of commutating current | $V_D = 400 \text{ V}$; $T_j = 150 \text{ °C}$; $I_{T(RMS)} = 12 \text{ A}$; $dV_{com}/dt = 20 \text{ V/}\mu\text{s}$; gate open circuit; "without snubber" condition | 2 | - | - | A/ms |
| | | $V_D = 400 \text{ V}$; $T_j = 150 \text{ °C}$; $I_{T(RMS)} = 12 \text{ A}$; $dV_{com}/dt = 10 \text{ V/}\mu\text{s}$; gate open circuit | 3.5 | - | - | A/ms |
| | | $V_D = 400 \text{ V}$; $T_j = 150 \text{ °C}$; $I_{T(RMS)} = 12 \text{ A}$; $dV_{com}/dt = 1 \text{ V/}\mu s$; gate open circuit | 5 | - | - | A/ms |
| t _{gt} | gate-controlled turn-on time | $I_{TM} = 20 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A/}\mu\text{s}$ | - | 2 | - | μs |

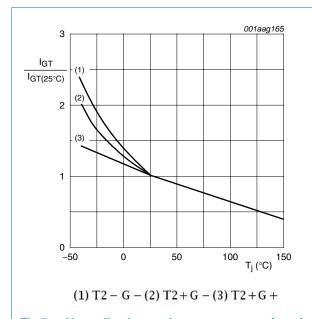


Fig 7. Normalized gate trigger current as a function of junction temperature

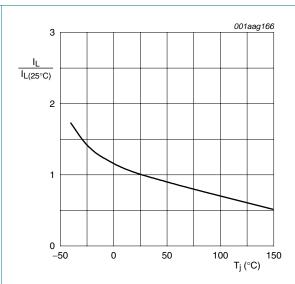


Fig 8. Normalized latching current as a function of junction temperature

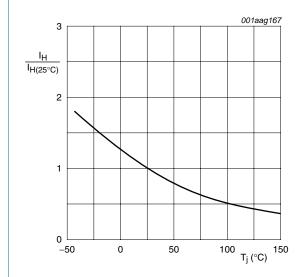
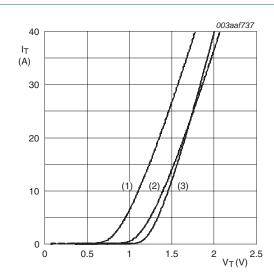


Fig 9. Normalized holding current as a function of junction temperature



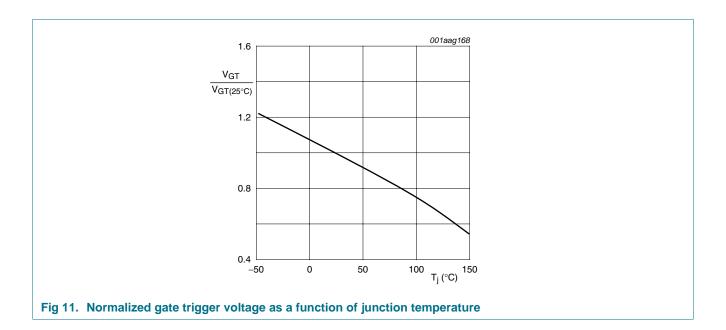
Vo = 1.127 V; Rs = 0.027 Ω

(1) Tj = 150 °C; typical values

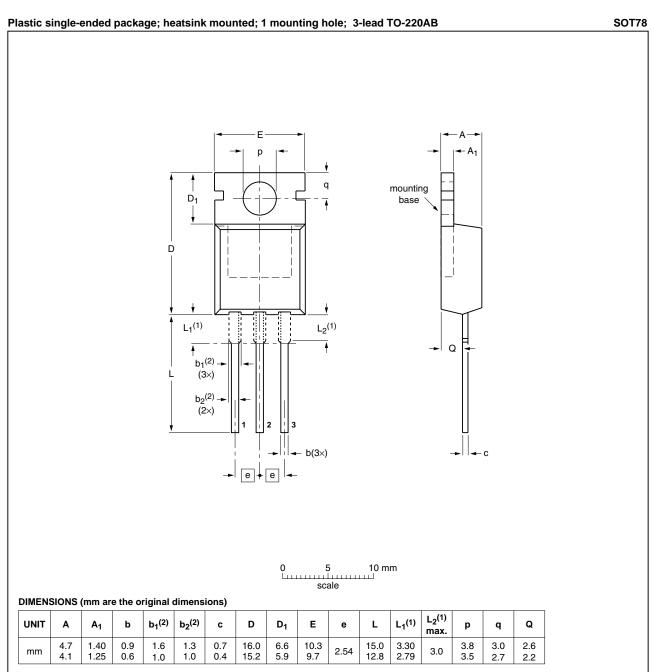
(2) Tj = 150 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage



7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|---------|-----|-----------------|-------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE |
| SOT78 | | 3-lead TO-220AB | SC-46 | | 08-04-23 08-06-13 |

Fig 12. Package outline SOT78 (TO-220AB)

BTA312-800ET

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|------------------------------------|--------------------|---------------|----------------------|
| BTA312-800ET v.2 | 20101202 | Product data sheet | - | BTA312_SER_CT_ET v.1 |
| Modifications: • Type number BTA312-800ET separated from data sheet BTA312_SER_CT_ET v.1. | | | | |
| | Various change | es to content. | | |
| BTA312_SER_CT_ET v.1 | 20070406 | Product data sheet | - | - |

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9.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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